

AMENDMENTS TO THE SPECIFICATION

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 2, line 25 as follows:

--Referring FIG.1A, a top view of a layer of indium tin oxide transparent conductive film 102 is formed on a glass substrate 100, in which the portion of slashes is a glass substrate 100 and the other portion is an ITO transparent conductive film 120. The ITO (indium tin oxide) transparent conductive film 120 is formed on glass substrate 100 by methods such as Thermal Evaporation Deposition, sputtering, Electron Beam Evaporation, Spray Pyrolysis, Chemical Vapor Deposition, and-or Pulsed Laser Deposition. In these methods, sputtering process has merits such as being able to form film of large square measure, film of even thickness, and reproducible thin film and is a process that is widely used at present. And through adjusting the parameters of film that forming in sputtering process such as distance between target material and glass substrate 100, thickness of thin film, and conditions of sputtering, the properties of ITO transparent conductive film 120 can be precisely controlled.--

Please amend the paragraph beginning on page 3, line 21 as follows:

--Since pi-type bus electrode 104 is composed ~~by~~ of silver and small sum of glass powder, there is good adhesion capability between portion of stripes 108 of the pi-type bus electrode 104 and glass substrate 100, but worse adhesion capability between the pi side 106 of the pi-type bus electrode 104 and ITO electrode 102. Therefore, the edge warp phenomenon of the pi side 106 of pi-type bus electrode 104 will occur, as shown in FIG.1C. And the edge warp phenomenon for the pi side 106 of pi-type bus electrode 104 will cause the point discharge effect of pi-type bus electrode, which hinders the following process to proceed.--

Please amend the paragraph beginning on page 4, line 6 as follows:

--In conventional art, a layer of edge warp preventer, which is not shown in the figure, is formed on pi-type bus electrode 104 before ~~it is~~ put under the firing process to prevent the edge warp phenomenon 110 of pi side 106 of pi-type bus electrode 104 ~~from occurring~~ occurred when ITO electrode 102 and pi-type bus electrode 104 are under the firing process. Although a preventer can be used to prevent the pi-type bus electrode from the edge warp phenomenon, yet the cost is getting higher and the process has complicated steps, which are the disadvantages of conventional solution.--

Please amend the paragraph beginning on page 4, line 22 as follows:

--Another purpose of the invention is to prevent the edge warp phenomenon occurred of the pi side of pi-type bus electrode.~~from occurring of edge warp phenomenon.~~--

Please amend the paragraph beginning on page 7, line 18 as follows:

--Then is one of the main features of the invention. Referring to FIG. 1B2B, a photoresist layer with a pattern of cavity (not shown in the drawing) is applied and is formed on ITO transparent conductive film 12. A portion of ITO transparent conductive film 12 on glass substrate 10 is then removed by wet etching method to form ITO electrode and ITO transparent conductive film 12 on pattern of cavity is also removed to expose portion of glass substrate 10 to form a cavity. The step of forming cavity 14 is to keep good adhesion capability between pi-type bus electrode formed in the following steps of the process (referring to FIG. 2C) and glass substrate 10, and therefore ~~improves the~~ adhesion capability between pi-type bus electrode 16 and ITO transparent conductive film 12 can be improved.--